Method For Forming A MIM Capacitor

Abstract

A method of manufacturing a MIM capacitor which is characterized as follows. We provide a semiconductor structure having a first region and a capacitor region. Next we form a first conductive layer over the semiconductor structure. The first conductive layer is patterned to form a plurality of trenches in the capacitor region. We form a capacitor dielectric layer over the first conductive layer. We form a top plate over the capacitor dielectric layer in the capacitor region. The first conductive layer in the first region is patterned to form conductive patterns and a bottom plate. An interlevel dielectric layer is formed over the first conductive layer and top plate.

FIGURE 10